

HY3008P/M/B/ MF /PL/PM

N-Channel Enhancement Mode MOSFET

Feature

80V/100A

$R_{DS(ON)} = 6.6m \text{ (typ.)}@V_{GS}$

Pin Description

TO-3PM-3L

YYXXX WW

G:Lead Free

Note: HUAYI lead

ation finish;which are fully compliant with RoHS. HUAYI lead

free peak reflow temperature. HUAYI defines

HUAYI

HY3008P/M/B/ MF /PL/PM

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		80	V
V _{GSS}	Gate-Source Voltage		±25	V
T _J	Maximum Junction Temperature		-55 to 175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	100	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	400**	A
I _D	Continuous Drain Current	Tc=25°C	100	A
		Tc=100°C	70	A
P _D	Maximum Power Dissipation	Tc=25°C	200	W
		Tc=100°C	100	W
R _{θJC}	Thermal Resistance, Junction-to-Case		0.75	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient **		62.5	°C/W
E _{AS}	SinglePulsed-Avalanche Energy ***	L=0.3 mH	407***	mJ

Note: * Repetitive rating pulse width limited by max.junction temperature.

** Surface mounted on 1in2 FR-4 board.

*** Limited by T_{Jmax}, starting T_J=25°C, L = 0.3mH, R_C= 25 , V_{GS}=10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3008			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} = 250 A	80	-	-	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} = 80V, V _{GS} =0V	-	-	1	A
		T _J =125°C	-	-	50	A
V _{GS(th)} I _{GSS}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} = 250 A	2	3	4	V

Electrical Characteristics (Cont.) (Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HY3008			Unit
			Min	Typ.	Max	
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.0	-	
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = 25V, Frequency=1.0MHz	-	3150	-	pF
C _{oss}	Output Capacitance					
C _{rss}	Reverse Transfer Capacitance					
t _{d(ON)}	Turn-on Delay Time	V _{DD} = 40V, R _G =3 Ω, I _{DS} = 50A, V _{GS} = 10V	-	23	-	ns
T _r	Turn-on Rise Time					
t _{d(OFF)}	Turn-off Delay Time					
T _f	Turn-off Fall Time					
Gate Charge Characteristics						
Q _g	Total Gate Charge	V _{DS} = 64V, V _{GS} = 10V, I _{DS} = 50A	-	67	-	nC
Q _{gs}	Gate-Source Charge					
Q _{gd}	Gate-Drain Charge					

Note: *Pulse test pulse width 300us duty cycle 2%

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Typical Operating Characteristics

Figure 1: Power Dissipation

Figure 2: Drain Current

Tc-Case Temperature()

Tc-Case Temperature()

Figure 3: Safe Operation Area

Figure 4: Thermal Transient Impedance

I_D-Drain Current(A)

I_D-Drain Current(A)

V_{DS}-Drain-Source Voltage(V)

Maximum Effective Transient Thermal Impedance, Junction-to-Case

Figure 5: Output Characteristics

Figure 6: Drain-Source On Resistance

I_D-Drain Current(A)

V_{DS}-Drain-Source Voltage (V)

I_D-Drain Current(A)

Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

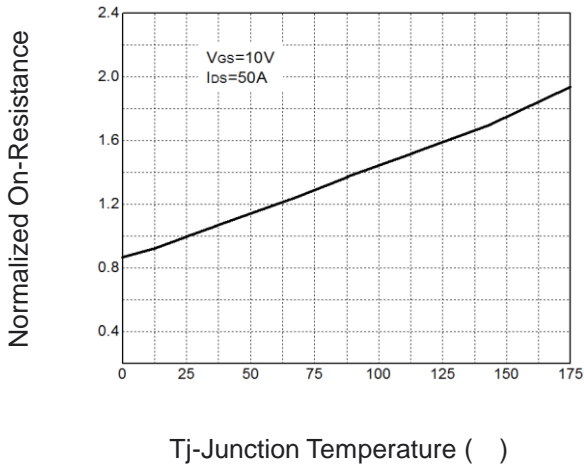


Figure 8: Source-Drain Diode Forward

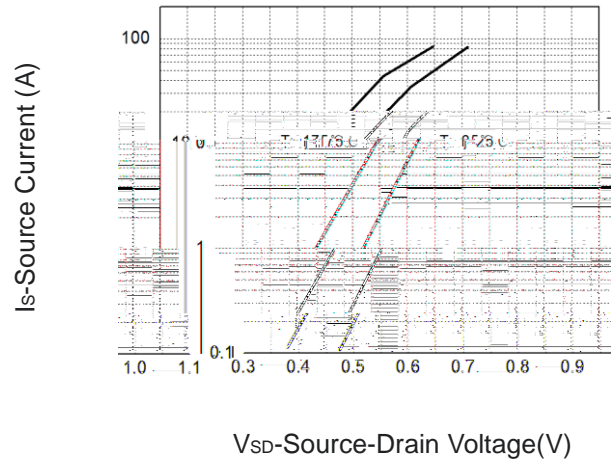


Figure 9: Capacitance Characteristics

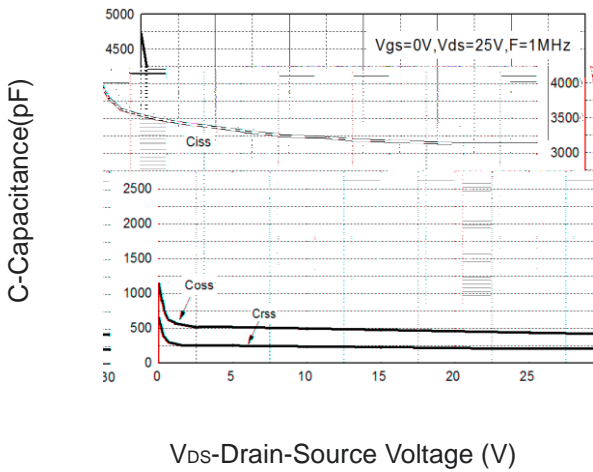
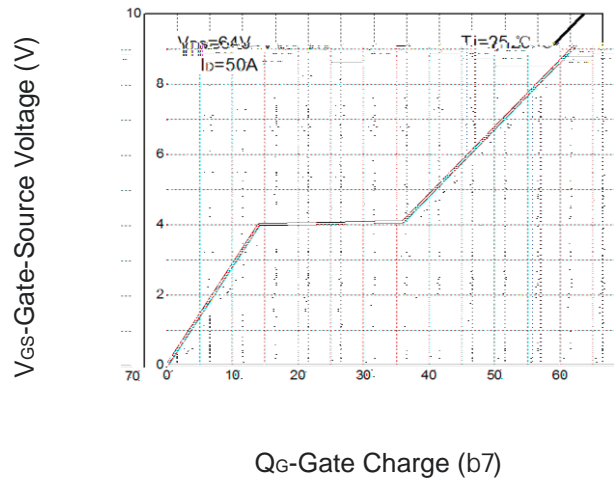
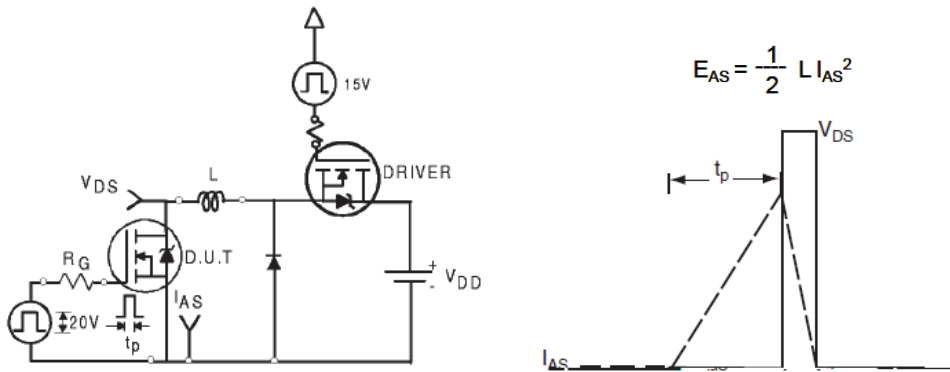


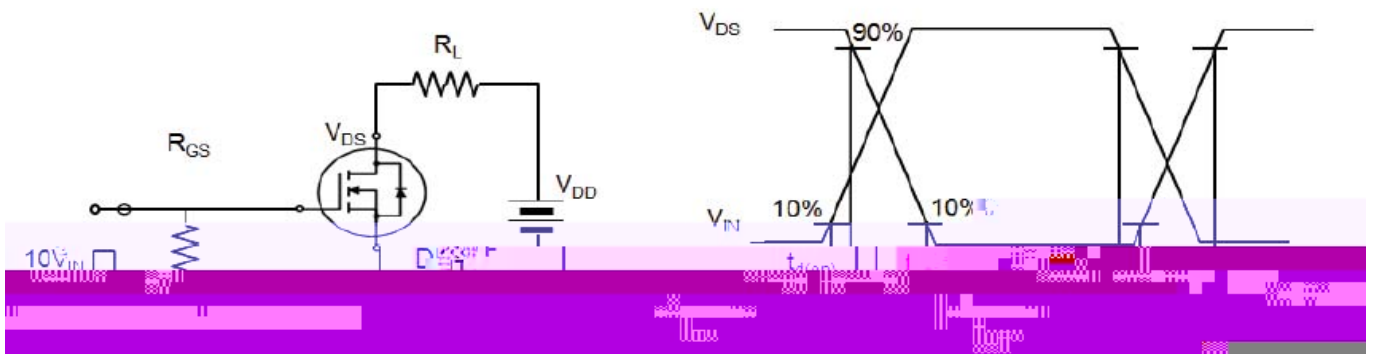
Figure 10: Gate Charge Characteristics



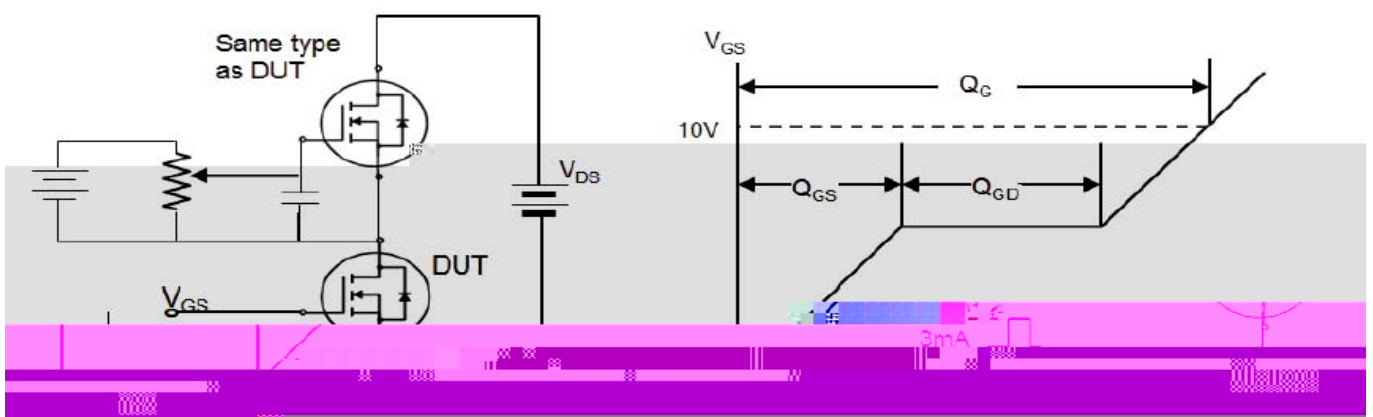
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

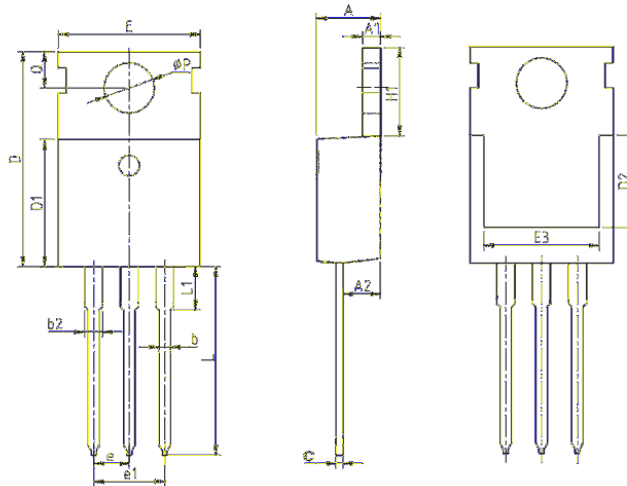


Device Per Unit

Package Type	Unit	Quantity
TO-220FB-3L	Tube	50

Package Information

TO-220FB-3L



COMMON DIMENSIONS

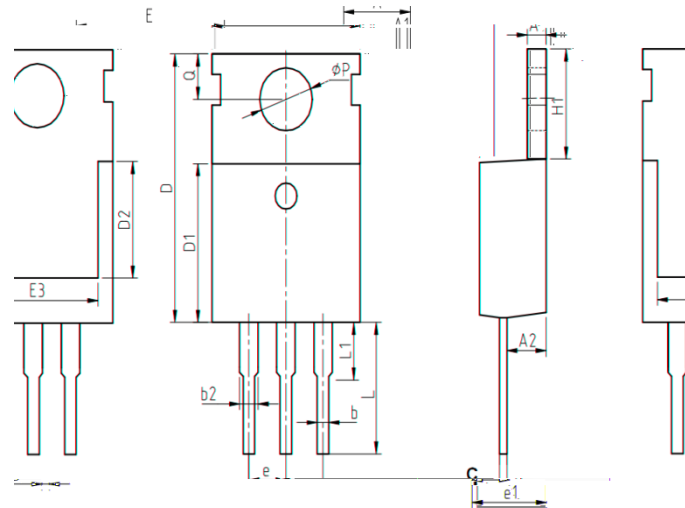
SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
P	3.40	3.60	3.80
Q	2.60	2.80	3.00

Device Per Unit

Package Type	Unit	Quantity
TO-220FB-3S	Tube	50

Package Information

TO-220FB-3S



COMMON DIMENSIONS

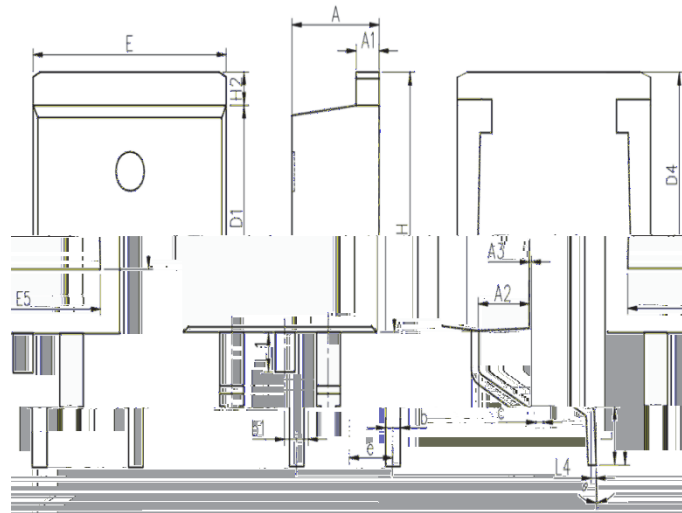
SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.25	1.30	1.45
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.40	0.50	0.65
D	15.10	15.60	16.10
D1	8.10	9.10	9.40
D2	5.50	-	-
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	6.80	7.00	7.20
L1	-	3.10	3.40
P	3.40	3.60	3.80
Q	2.60	2.80	3.00

Device Per Unit

Package Type	Unit	Quantity
TO-263-2L	Reel	50

Package Information

TO-263-2L



COMMON DIMENSIONS

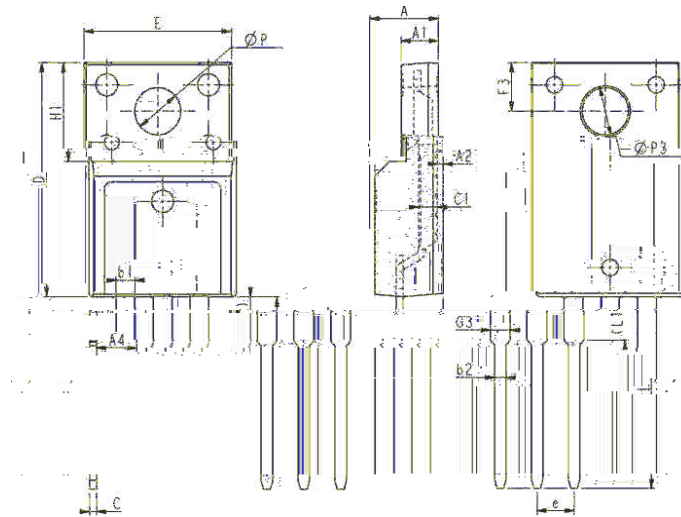
SYMBOL	mm		
	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0	0.13	0.25
b	0.7	0.81	0.96
b1	1.17	1.27	1.47
c	0.3	0.38	0.53
D1	8.5	8.7	8.9
D4	6.6	-	-
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54 BSC		
H	14.7	15.1	15.5
H2	1.07	1.27	1.47
L	2	2.3	2.6
L1	1.4	1.55	1.7
L4	0.25 BSC		
	0°	5°	9°

Device Per Unit

Package Type	Unit	Quantity
TO-220MF-3L	Tube	50

Package Information

TO-220MF-3L



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
P	3.03	3.18	3.38
P3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95

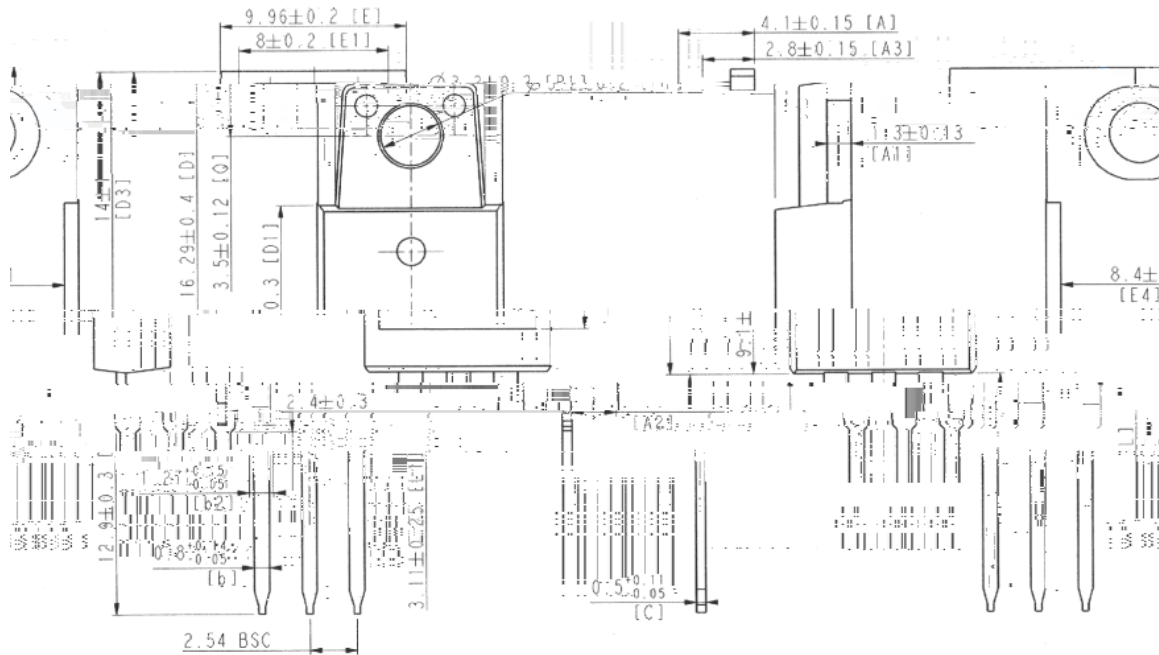
HY3008P/M/B/ MF /PL/PM

Device Per Unit

Package Type	Unit	Quantity
TO-3PM-3L	Tube	50

Package Information

TO-3PM-3L



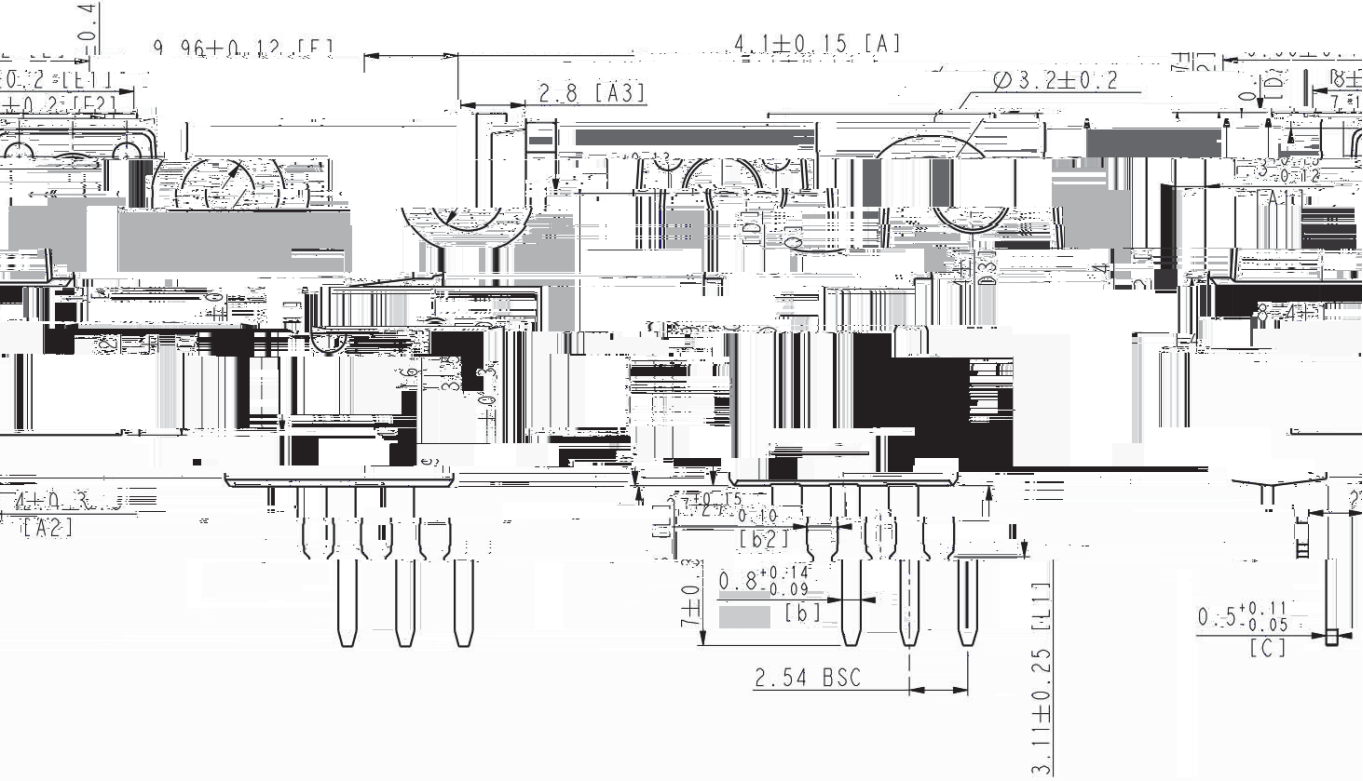
HY3008P/M/B/ MF /PL/PM

Device Per Unit

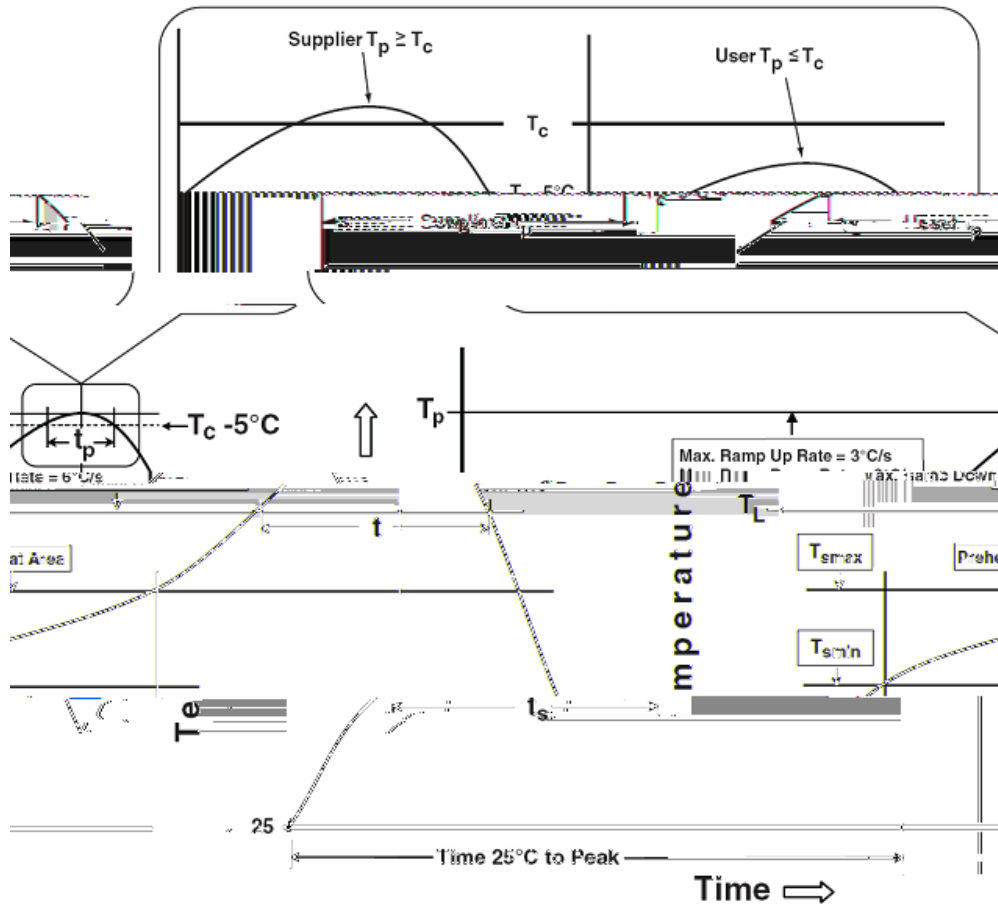
Package Type	Unit	Quantity
TO-3PM-3S	Tube	50

Package Information

TO-3PM-3S



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.

*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.

** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.

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Table 1.SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350
2.5 mm	235 °C	220 °C
2.5 mm	220 °C	220 °C

Table 2.Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm <350	Volume mm 350-2000	Volume mm 2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	168 Hrs /500 Hrs /1000 Hrs, Bias @ 150°C
PCT	JESD-22, A102	96 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -55°C~150°C